ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE6251 & NTE6252
Silicon Rectifier
Dual, Positive Center Tap

Features:
- Dual Rectifier Construction, Positive Center Tap
- Low Forward Voltage, High Current Capability
- Low Thermal Resistance
- Low Power Loss

Maximum Ratings and Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Maximum Repetitive Peak Reverse Voltage, V_{RRM}
- NTE6251 . . . . . 200V
- NTE6252 . . . . . 600V

Maximum RMS Voltage, V_{RMS}
- NTE6251 . . . . . 140V
- NTE6252 . . . . . 420V

Maximum DC Blocking Voltage, V_{DC}
- NTE6251 . . . . . 200V
- NTE6252 . . . . . 600V

Maximum Average Forward Rectified Current (T_C = +100°C), $I_{F(AV)}$ 30A

Peak Forward Surge Current, I_{FSM}
- (8.3ms Single Half Sine–Wave Superimposed on Rated Load) 300A

Maximum Instantaneous Forward Voltage (Per Leg at 15A), V_F
- NTE6251 . . . . . 0.95V
- NTE6252 . . . . . 1.5V

Maximum DC Reverse Current (At Rated V_{DC}), I_R
- T_C = +25°C 10µA
- T_C = +100°C 500µA

Maximum Reverse Recovery Time (Per Leg, Note 1), t_{rr}
- NTE6251 . . . . . 35ns
- NTE6252 . . . . . 50ns

Typical Junction Capacitance (Per Leg, Note 2), C_J
- NTE6251 . . . . . 175pF
- NTE6252 . . . . . 145pF

Thermal Resistance, Junction–to–Case (Note 3), R_{thJC} . . . . . 1.0°C/W

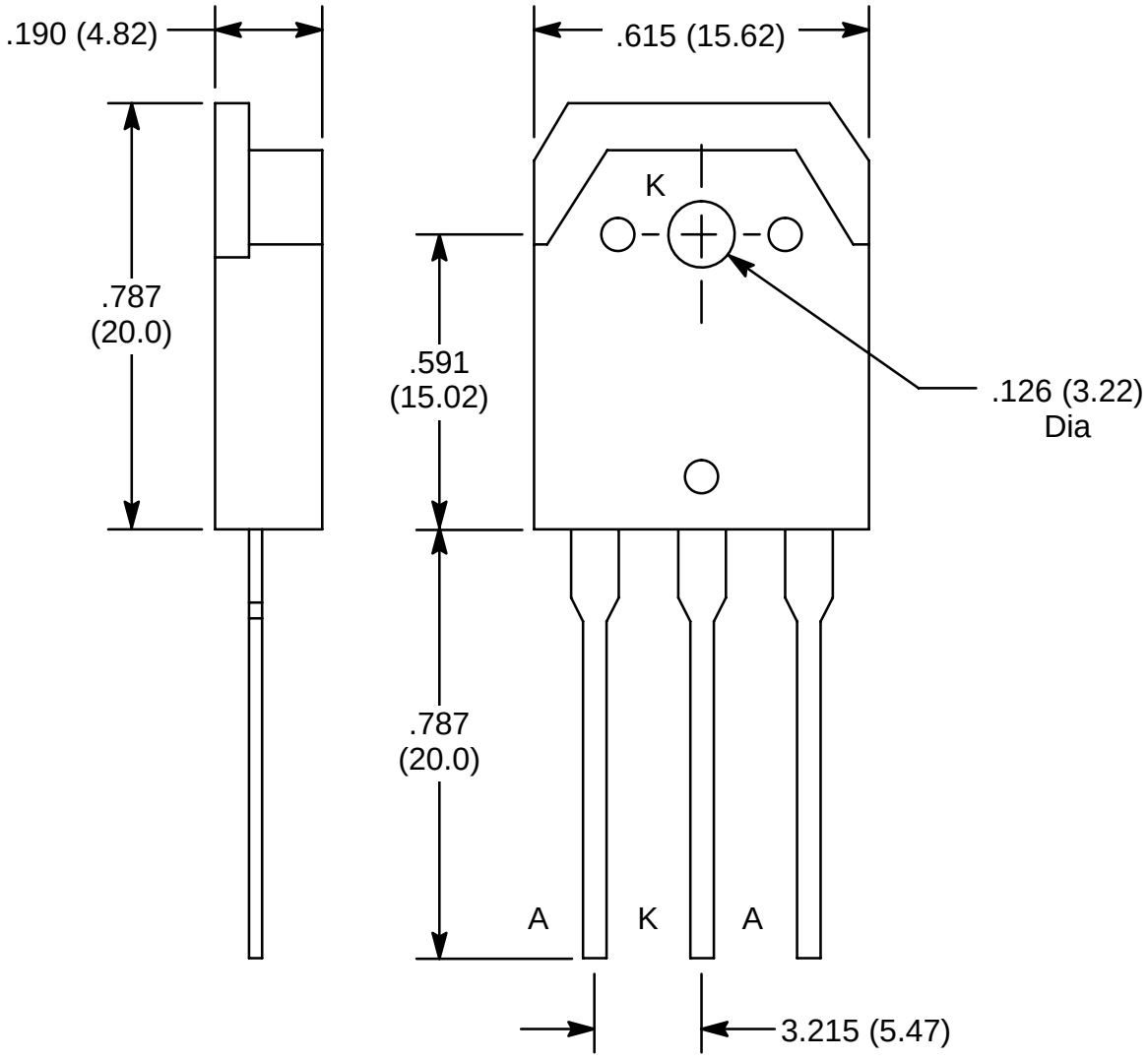
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C

Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Note 1. Reverse Recovery test conditions: I_F = 0.5A, I_R = 1A, I_{rr} = 0.25A.

Note 2. Measured at 1MHz and applied reverse voltage of 4V.

Note 3. Thermal resistance from junction to case per leg mounted on a heatsink.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